NTR4502P, NVTR4502P

Power MOSFET

−30 V, −1.95 A, Single, P−Channel, SOT−23

ON Semiconductor®

http://onsemi.com

$V_{(BR)DSS}$	$R_{DS(on)}$ TYP	I_D Max (Note 1)
−30 V	155 mΩ @ −10 V	−1.95 A
	240 mΩ @ −4.5 V	

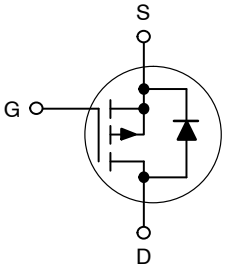
Features

- Leading Planar Technology for Low Gate Charge / Fast Switching
- Low $R_{DS(ON)}$ for Low Conduction Losses
- SOT−23 Surface Mount for Small Footprint (3 X 3 mm)
- AEC Q101 Qualified − NVTR4502P
- These Devices are Pb−Free and are RoHS Compliant

Applications

- DC to DC Conversion
- Load/Power Switch for Portables and Computing
- Motherboard, Notebooks, Camcorders, Digital Camera's, etc.
- Battery Charging Circuits

P−Channel MOSFET



MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

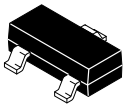
Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	−30	V
Gate−to−Source Voltage			V_{GS}	±20	V
Drain Current (Note 1)	t < 10 s	T_A = 25°C	I_D	−1.95	A
		T_A = 70°C		−1.56	
Power Dissipation (Note 1)	t < 10 s		P_D	1.25	W
Continuous Drain Current (Note 1)	Steady State	T_A = 25°C	I_D	−1.13	A
		T_A = 70°C		−0.90	
Power Dissipation (Note 1)	Steady State		P_D	0.4	W
Pulsed Drain Current	t_p = 10 μs		I_{DM}	−6.8	A
Operating Junction and Storage Temperature			T_J, T_{STG}	−55 to 150	°C
Source Current (Body Diode)			I_S	−1.25	A
Lead Temperature for Soldering Purposes (1/8 in from case for 10 s)			T_L	260	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction−to−Ambient − Steady State (Note 1)	$R_{\theta JA}$	300	°C/W
Junction−to−Ambient − t = 10 s (Note 1)	$R_{\theta JA}$	100	

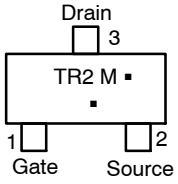
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface−mounted on FR4 board using 1 in sq. pad size (Cu area = 1.127 in sq. [1 oz] including traces).



SOT−23
CASE 318
STYLE 21

MARKING DIAGRAM/ PIN ASSIGNMENT



TR2 = Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
NTR4502PT1G	SOT−23 (Pb−Free)	3000 / Tape & Reel
NVTR4502PT1G	SOT−23 (Pb−Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Electrical Characteristics (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = −250 μA		−30			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = −30 V	T_J = 25°C			−1	μA
			T_J = 55°C			−10	
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V				±100	nA
ON CHARACTERISTICS (Note 3)							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = −250 μA		−1.0		−3.0	V
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = −10 V, I_D = −1.95 A			155	200	mΩ
		V_{GS} = −4.5 V, I_D = −1.5 A			240	350	
Forward Transconductance	g_{FS}	V_{DS} = −10 V, I_D=−1.25 A			3		S
CHARGES AND CAPACITANCES							
Input Capacitance	C_{ISS}	V_{GS} = 0 V, f = 1 MHz, V_{DS} = −15 V			200		pF
Output Capacitance	C_{OSS}				80		
Reverse Transfer Capacitance	C_{RSS}				50		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = −10 V, V_{DS} = −15 V; I_D = −1.95 A			6	10	nC
Threshold Gate Charge	$Q_{G(TH)}$				0.3		
Gate−to−Source Charge	Q_{GS}				1		
Gate−to−Drain Charge	Q_{GD}				1.7		
SWITCHING CHARACTERISTICS (Note 4)							
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} =−10 V, V_{DD} = −15 V, I_D = −1.95 A, R_G = 6 Ω			5.2	10	ns
Rise Time	t_r				12	20	
Turn−Off Delay Time	$t_{d(OFF)}$				19	35	
Fall Time	t_f				17.5	30	
DRAIN−SOURCE DIODE CHARACTERISTICS (Note 3)							
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = −1.25 A			−0.8	−1.2	V
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, dI_{SD}/d_t = 100 A/μs, I_S = −1.25 A			23		ns

2. Surface−mounted on FR4 board using 1 in sq. pad size (Cu area = 1.127 in sq. [1 oz] including traces).
3. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
4. Switching characteristics are independent of operating junction temperatures.

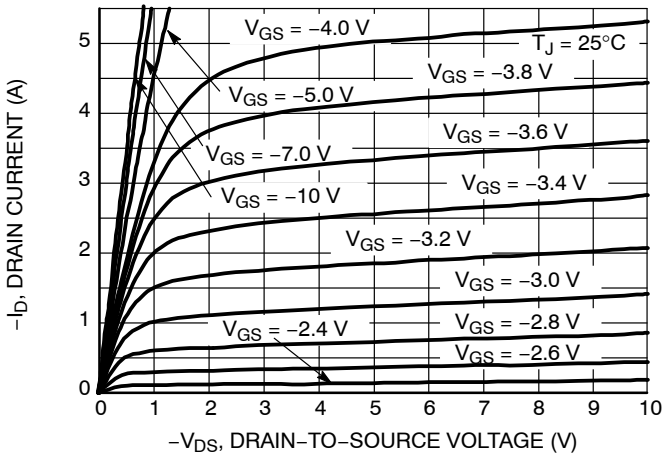


Figure 1. On−Region Characteristics

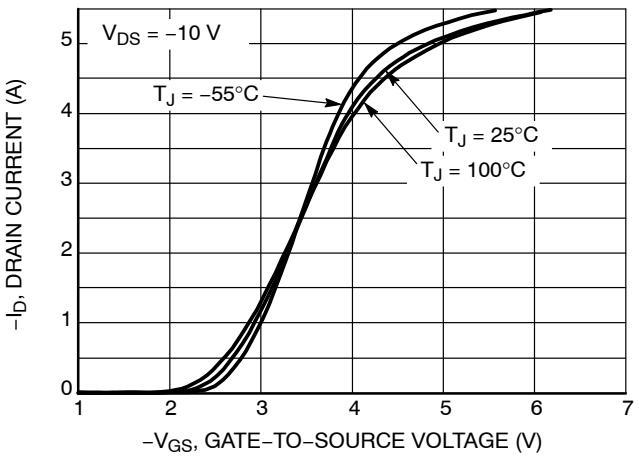


Figure 2. Transfer Characteristics

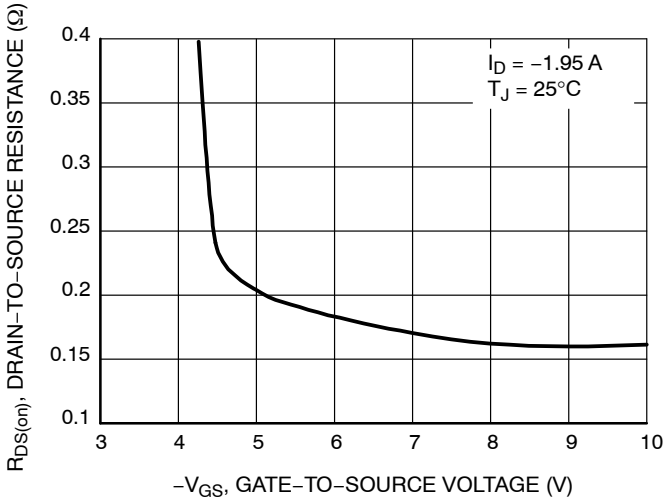


Figure 3. On−Resistance versus Gate−to−Source Voltage

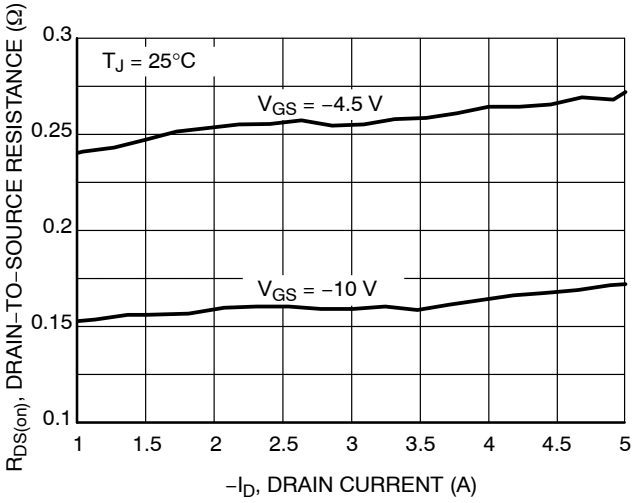


Figure 4. On−Resistance versus Drain Current and Gate Voltage

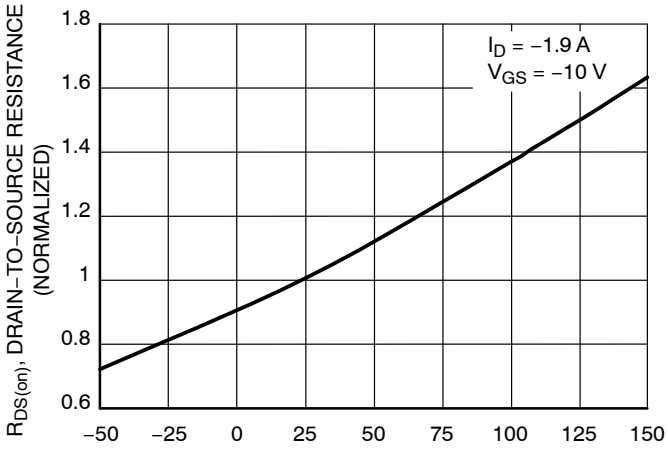


Figure 5. On−Resistance Variation with Temperature

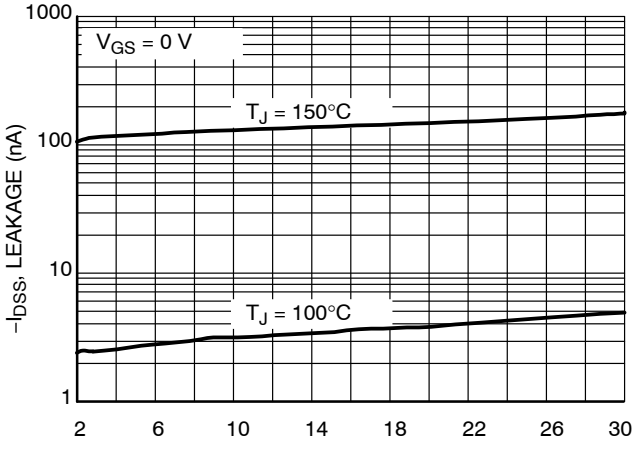


Figure 6. Drain−to−Source Leakage Current versus Voltage

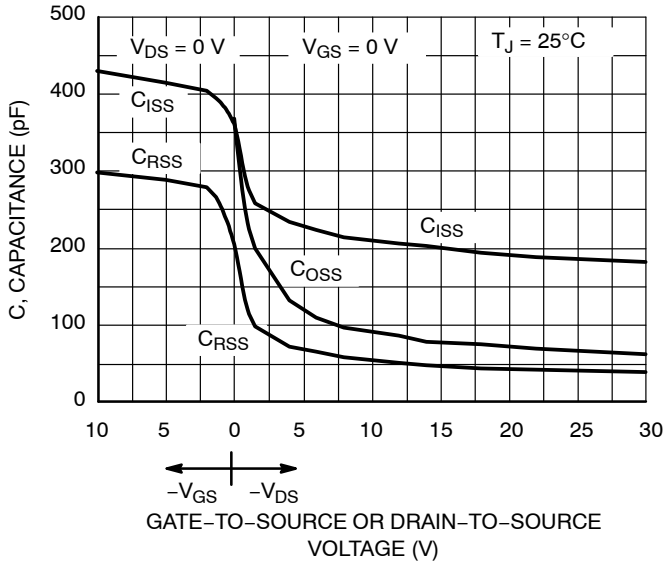


Figure 7. Capacitance Variation

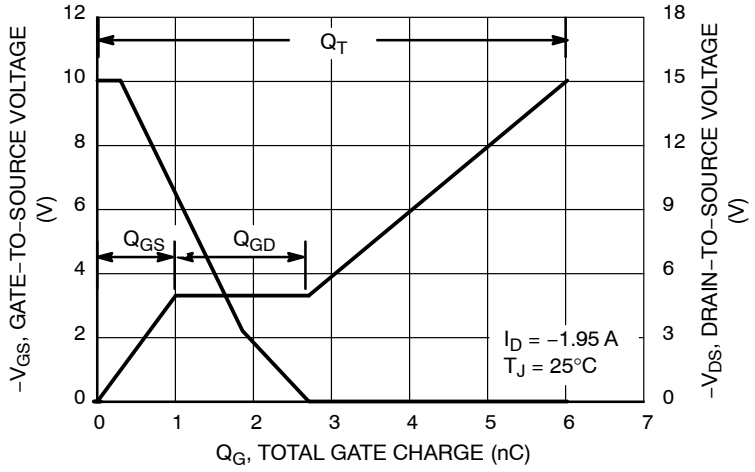


Figure 8. Gate−to−Source and Drain−to−Source Voltage versus Total Charge

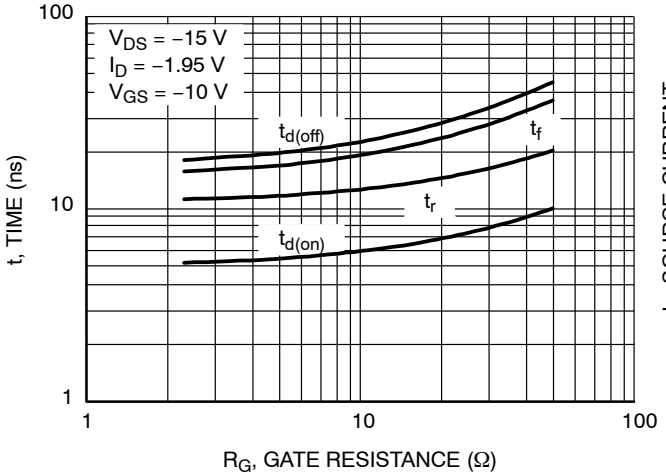


Figure 9. Resistive Switching Time Variation versus Gate Resistance

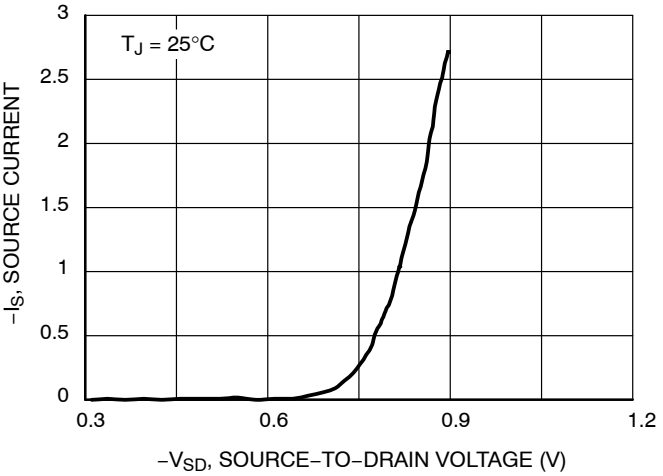
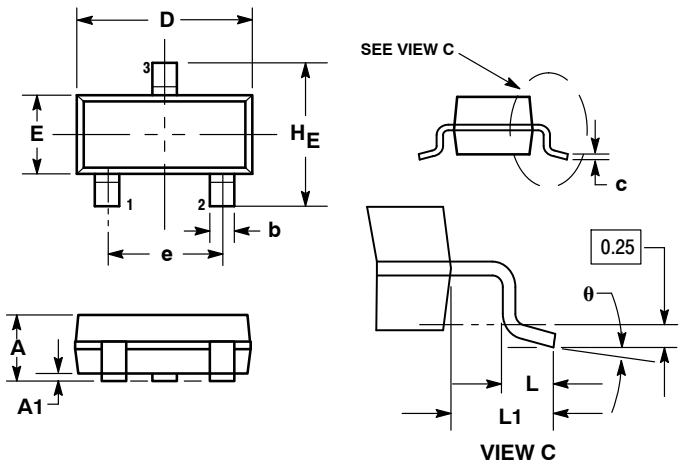


Figure 10. Diode Forward Voltage versus Current

PACKAGE DIMENSIONS

SOT−23 (TO−236)
CASE 318−08
ISSUE AP

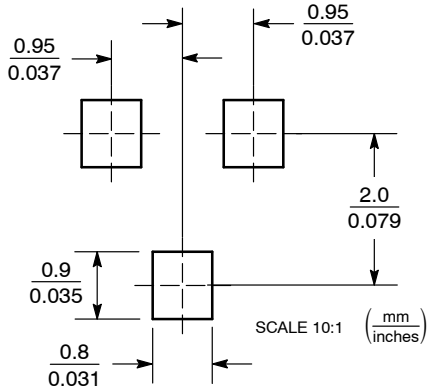


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
H_E	2.10	2.40	2.64	0.083	0.094	0.104
θ	0°	−−−	10°	0°	−−−	10°

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
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